

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device comprising:

providing a substrate having an insulating layer and a single crystal silicon layer formed on the insulating layer;

forming a strain-inducing semiconductor layer on the single crystal silicon layer, the strain-inducing semiconductor having ~~the a~~ lattice constant differing from ~~the a~~ lattice constant of the single crystal silicon layer;

matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer and changing the single crystal silicon layer into a strained silicon layer, by providing an annealing process with respect to the single crystal silicon layer and the strain-inducing semiconductor layer without performing ion implantation in the single crystal silicon layer and the strain-inducing semiconductor layer~~by matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer; and~~

removing the strain-inducing semiconductor layer.

2. (Canceled)

3. (Currently amended) The method of manufacturing a semiconductor device as defined in claim 1,

wherein ~~when a~~the single crystal silicon layer is provided with the strain-inducing semiconductor layer formed on the strain-inducing semiconductor layer thereon, wherein the single crystal silicon layer ~~on the strain-inducing semiconductor layer~~ has a thickness ~~which causes no defects~~such that no defect occurs in the strain-inducing semiconductor layer.

4. (Original) The method of manufacturing a semiconductor device as defined in claim 1,

wherein a layer including germanium is formed as the strain-inducing semiconductor layer.

5. (Original) The method of manufacturing a semiconductor device as defined in claim 1,

wherein the strain-inducing semiconductor layer is removed by wet etching using mixed acid of hydrofluoric acid and nitric acid.

6. (Original) The method of manufacturing a semiconductor device as defined in claim 1,

wherein the step of forming the strain-inducing semiconductor layer is performed by using a metal organic chemical vapor deposition method, a molecular beam epitaxy method, or a ultra high vacuum chemical vapor deposition method.

7. (Currently Amended) The method of manufacturing a semiconductor device as defined in ~~claim 2~~claim 1,

wherein the annealing process is performed through a temperature increase process, a constant temperature process, and a temperature decrease process.

8. (Withdrawn) A semiconductor device comprising:  
a semiconductor substrate manufactured by the method of manufacturing a semiconductor device as defined in claim 1.

9. (Withdrawn) A semiconductor device comprising:  
a semiconductor substrate which includes an insulating layer and a strained silicon layer formed on the insulating layer; and  
a field effect transistor formed on the semiconductor substrate.

10. (New) A method of manufacturing a semiconductor device comprising:
  - providing a substrate having an insulating layer and a single crystal silicon layer formed on the insulating layer;
  - forming a strain-inducing semiconductor layer on the single crystal silicon layer, the strain-inducing semiconductor having a lattice constant differing from a lattice constant of the single crystal silicon layer;
  - changing the single crystal silicon layer into a strained silicon layer, by cutting a Si-Si bond of the single crystal silicon layer through providing an annealing process and matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer; and
  - removing the strain-inducing semiconductor layer.